

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
23 June 2005 (23.06.2005)

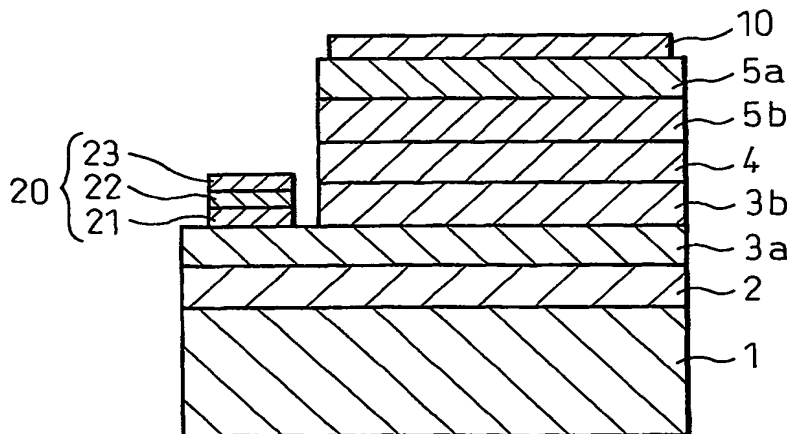
PCT

(10) International Publication Number
WO 2005/057642 A1

- (51) International Patent Classification⁷: **H01L 21/28**, 33/00
- (21) International Application Number: PCT/JP2004/018689
- (22) International Filing Date: 8 December 2004 (08.12.2004)
- (25) Filing Language: English
- (26) Publication Language: English
- (30) Priority Data:
2003-412236 10 December 2003 (10.12.2003) JP
60/529,751 17 December 2003 (17.12.2003) US
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- (81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.
- (84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).
- Published:
— with international search report

[Continued on next page]

(54) Title: GALLIUM NITRIDE-BASED COMPOUND SEMICONDUCTOR LIGHT-EMITTING DEVICE AND NEGATIVE ELECTRODE THEREOF



(57) Abstract: An object of the present invention is to provide a negative electrode which attains excellent Ohmic contact with an n-type gallium nitride-based compound semiconductor layer and which resists deterioration in characteristics which would be caused by heating. Another object of the invention is to provide a gallium nitride-based compound semiconductor light-emitting device having the negative electrode. The inventive gallium nitride-based compound semiconductor light-emitting device comprises an n-type semiconductor layer of a gallium nitride-based compound semiconductor, a light-emitting layer of a gallium nitride-based compound semiconductor and a p-type semiconductor layer of a gallium nitride-based compound semiconductor formed on a substrate in this order, and has a negative electrode and a positive electrode provided on the n-type semiconductor layer and the p-type semiconductor layer, respectively; wherein the negative electrode comprises a bonding pad layer and a contact metal layer which is in contact with the n-type semiconductor layer, and the contact metal layer is composed of Cr or a Cr alloy and formed through sputtering.

WO 2005/057642 A1



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